

SEMICONDUCTOR STRUCTURE AND METHOD FOR MANUFACTURING SAME, MEMORY AND OPERATION METHOD THEREOF

ABSTRACT

Provided are a semiconductor structure and a method for manufacturing the same, a memory and a method for operating the same. The semiconductor structure includes a substrate having a plurality of active areas close to a surface of the substrate; a gate structure located in a first structure layer on the substrate, in which the gate structure and the active areas constitute a selective transistor; and an anti-fuse bit structure located in a second structure layer on the first structure layer, and connected with an active area of one selective transistor through a first connecting structure, in which a breakdown state and a non-breakdown state of the anti-fuse bit structure represent different stored data.

[Fig. 3]